



Docket No.  
87552.99R134/SE-906D

A6  
Aug 2000  
3/16/00

IN THE UNITED STATES PATENT & TRADEMARK OFFICE

Applicant :	Linn et al.	) Examiner:
		) S. Loke
Serial No. :	09/316,580	)
Filed :	May 21, 1999	) Art Unit:
For :	BONDED WAFER WITH METAL SILICIDATION	) 2811
		)
		)
		)
		)

AMENDMENT UNDER 37 CFR §1.116  
AND REQUEST FOR RECONSIDERATION

Assistant Commissioner for Patents  
Washington, D.C. 20231  
Box AF

Dear Sir:

In response to the Office Action mailed January 6, 2000, please amend the above-identified application as follows:

In the Claims:

Amend claim 4 as follows:

4. (Amended) The integrated circuit of claim [1] 7 wherein said device silicon layer includes deep buried layers abutting said second dielectric layer.

Amend claim 5 as follows:

5. (Amended) The integrated circuit of claim [1]7 wherein said handle [wafer] die comprises silicon and [at least one of said dielectric dielectric layers] said first dielectric layer comprises diamond.

Further amend claim 10 as follows:

10. (Twice amended) A bonded wafer integrated circuit comprising:

(a) a handle die comprising a first dielectric layer, said first dielectric layer comprising a first bonding material;